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Sheet 1 of 1

Complete if Known	
Application Number	10/677,643
Filing Date	10/01/2003
First Named Inventor	TOMISLAV SULIGOJ
Art Unit	2826
Examiner Name	QUACH
Attorney Docket Number	UC01-332-2US

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
AA		P. BILJANOVIC, T. SULIGOJ, "Horizontal Current Bipolar Transistor (HCBT): A New Concept of Silicon Bipolar Transistor Technology", IEEE Trans. on Electron Devices, 1 Nov. 2001, pp 2551-2554, vol. 48	
AA		R. GOMEZ, R. BASHIR, G.W. NEUDECK, "On the design and fabrication of novel lateral bipolar transistor in a deep-submicorn technology", Microelectronics Journal, March 2000, pp 199-205, vol. 31	
AA		R. DEKKER, P. BALTUS, M. VAN DEURZEN, W V.D. EINDEN, H. MAAS, A. WAGEMANS, "An Ultra Low-Power RF Bipolar Technology on Glass", International Electron Devices Meeting Tech. Dig., December 1997 pp. 921-923	
AA		H. NII, T. YAMADA, K. INOH, T. SHINO, S. KAWANAKA, M. YOSHIMI, Y. KATSUMATA, "A Novel Lateral Bipolar Transistor with 67 GHz fmax on Thin-Film SOI for RF Analog Applications" IEEE Trans. Electron Devices, July 2000, pp. 1536-1541, vol. 47	
AA		T. SHIBA, Y. TAMAKI, T. ONAI, Y. KIYOTA, T. KURE, T. NAKAMURA, "A Very Small Bipolar Transistor Technology with Sidewall Polycide Base Electrode for ECL-CMOS LSI's", IEEE Trans. Electron Devices, Sept. 1996, pp. 1357-1363, vol. 43.	
AA		S. KONAKA, M. UGAJIN, T. MATSUDA, "Deep Submicrometer Super Self-Aligned Si Bipola Technology with 25.4 ps ECL", IEEE Trans. Electron Devices, Jan. 1994, pp 44-49, vol. 41	

Examiner Signature		Date Considered	5/6/05

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